

2SK1772

Silicon N Channel MOS FET

REJ03G0971-0200

(Previous: ADE-208-1318)

Rev.2.00 Sep 07, 2005

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source.
- Suitable for DC-DC converter, motor drive, power switch, solenoid drive

Outline



*UPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	1	Α
Drain peak current	I _{D(pulse)} *1	2	Α
Body to drain diode reverse drain current	I _{DR}	1	Α
Channel dissipation	Pch ^{*2}	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

2. When using the alumina ceramic board (12.5 \times 20 \times 0.7mm)

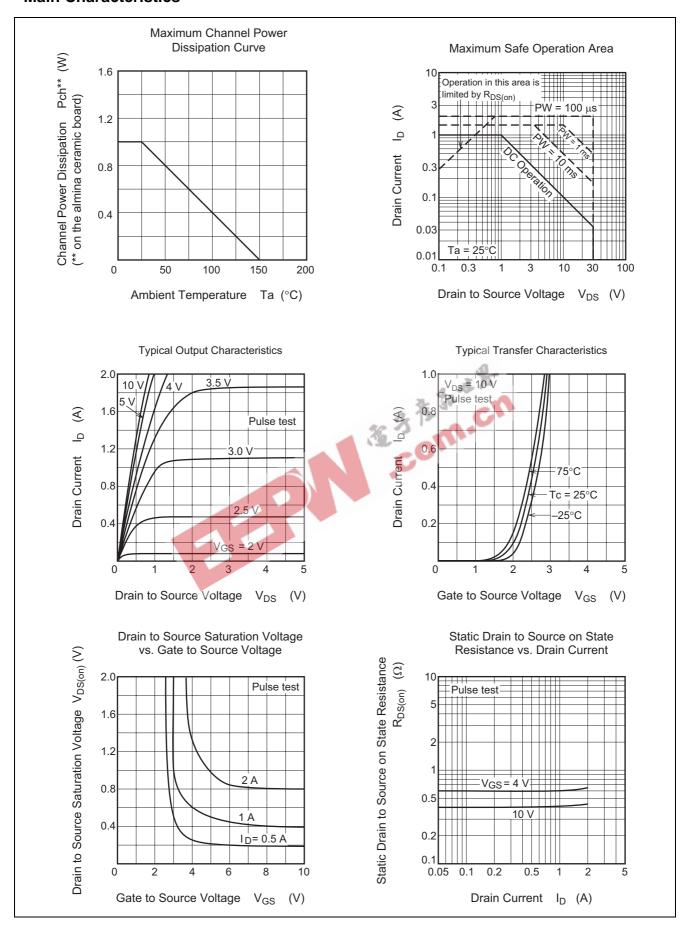
Electrical Characteristics

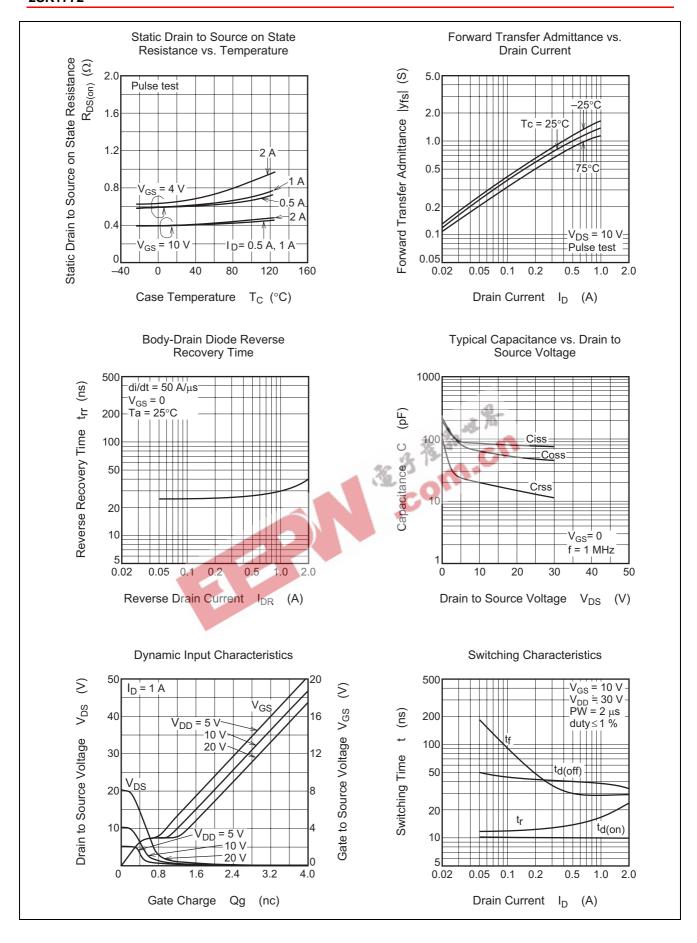
 $(Ta = 25^{\circ}C)$

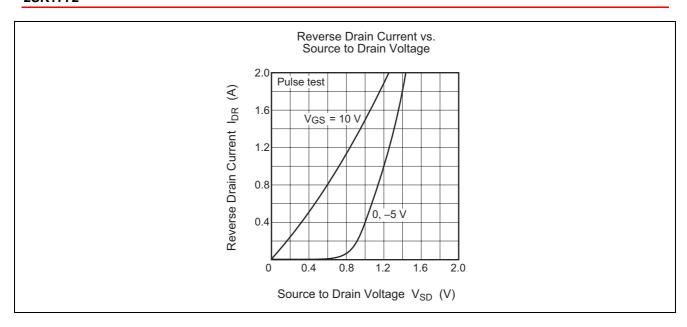
Item	Symbol	Min	Тур	Max	Unit	Test Conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	-		V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20			V	$I_G=\pm 100~\mu\text{A},~V_{DS}=0$	
Gate to source leak current	I _{GSS}	_		±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$	
Zero gate voltage drain current	I _{DSS}	-		50	μΑ	$V_{DS} = 25 \text{ V}, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$	
Static drain to source on state	R _{DS(on)}	-	0.4	0.6	Ω	$I_D = 0.5 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$	
resistance		_	0.6	0.85	Ω	$I_D = 0.5 \text{ A}, V_{GS} = 4 \text{ V}^{*3}$	
Forward transfer admittance	y _{fs}	0.6	1.0	~ O	S	$I_D = 0.5 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$	
Input capacitance	Ciss	1	8 5	5	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$	
Output capacitance	Coss	1 17	65	_	pF	f = 1 MHz	
Reverse transfer capacitance	Crss	4	20	_	pF		
Turn-on delay time	t _{d(on)}		10	_	ns	$I_D = 0.5 \text{ A}, V_{GS} = 10 \text{ V},$	
Rise time	t _r	_	15	_	ns	$R_{L} = 60 \ \Omega^{*3}$	
Turn-off delay time	t _{d(off)}	_	40	_	ns		
Fall time	t _f	_	30	_	ns		
Body to drain diode forward voltage	V _{DF}	_	1.2	_	V	$I_F = 1 \text{ A}, V_{GS} = 0^{*3}$	
Body to drain diode reverse	t _{rr}	_	30	_	ns	$I_F = 1 A, V_{GS} = 0,$	
recovery time						$di_{F}/dt = 50 \text{ A}/\mu\text{s}^{*3}$	

Note: 3. Pulse Test

Main Characteristics

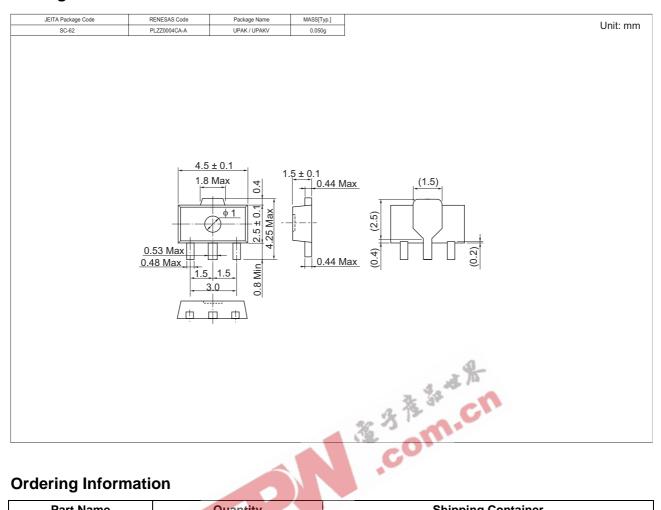








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1772HYTR-E	3000 pcs	Taping, φ178 mm Reel

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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